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<b>1 P E</b> <b>INFORMATION DISCLOSURE</b> <b>STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		Application Number	09/924,872
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		First Named Inventor	Hiroyuki NAGASAWA
		Art Unit	2812
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Sheet	1	of	1
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		Q65781	

## **U.S. PATENT DOCUMENTS**

## FOREIGN PATENT DOCUMENTS

#### **OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
GJ		R.S. Kem et al.; "Deposition and Doping of Silicon Carbide By Gas-Source Molecular Beam Epitaxy"; Appl. Phys. Lett. 71 (10); September 8, 1997; pp. 1356-1358.	
GJ		Jin-Hyo Boo et al.; "Low-Temperature Epitaxial Growth of Cubic SiC Thin Films On Si(111) Using Supersonic Molecular Jet of Single Source Precursors"; Thin Solid Films 343-344 (1999); pp. 650-655.	
GJ		Tatsuo YOSHINOBU et al.; "Atomic Level Control In Gas Source MBE Growth of Cubic SiC"; Journal of Crystal Growth; Nos. 1-4; Part I; January 1990; pp. 520-524.	
GJ		Tsunenobu Kimoto et al.; "Incorporation Mechanism of N, Al, and B Impurities in Chemical Vapor Deposition of SiC"; Applied Physics Letters; No. 16; October 16, 1995; pp. 2385-2387.	
GJ		J.J. Sumakeris et al.; "Layer-By-Layer Growth of SiC at Low Temperatures"; Thin Solid Films; No. 1-2; March 25, 1993; pp. 219-224.	
GJ		V. Cimalla et al.; "Growth of Thin $\beta$ -SiC Layers by Carbonization of Si Surfaces by Rapid Thermal Processing"; Materials Science & Engineering B Solid-State Materials for Advanced Technology; Nos. 1-3; January 1995; pp. 170-175.	

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